### BC636/638/640

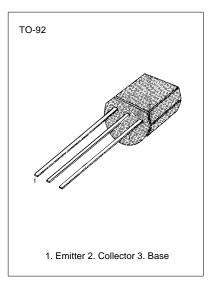
# PNP EPITAXIAL SILICON TRANSISTOR

### SWITCHING AND AMPLIFIER APPLICATIONS

Complement to BC635/637/639

### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C)

Characteristic	Symbol	Rating	Unit	
Collector Emitter Voltage	: BC636	V <sub>CER</sub>	-45	V
at R <sub>BE</sub> =1Kohm	: BC638		-60	V
	: BC640		-100	V
Collector Emitter Voltage	: BC636	V <sub>CES</sub>	-45	V
	: BC638		-60	V
	: BC640		-100	V
Collector Emitter Voltage	: BC636	V <sub>CEO</sub>	-45	V
	: BC638		-60	V
	: BC640		-80	V
Emitter Base Voltage		V <sub>EBO</sub>	-5	V
Collector Current		I <sub>C</sub>	-1	Α
Peak Collector Current		I <sub>CP</sub>	-1.5	А
Base Current		IB	-100	mA
Collector Dissipation		Pc	1	W
Junction Temperature		TJ	150	°C
Storage Temperature		T <sub>STG</sub>	-65 ~ 150	°C



### ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C)

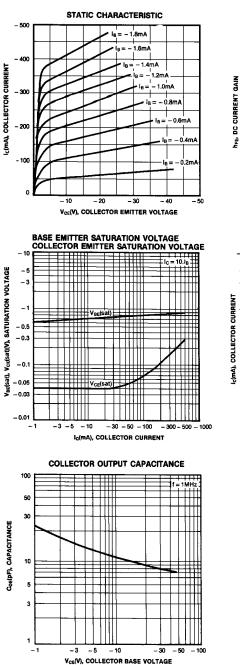
Characteristic	Symbol	Test Conditions	Min	Тур	Max	Unit
Collector-Emitter Breakdown Voltage : BC636 : BC638 : BC640 Collector Cut-off Current Emitter Cut-off Current DC Current Gain : BC635 : BC637/BC639 Collector Emitter Saturation Voltage Base Emitter On Voltage Current Gain Bandwidth Product	$\begin{array}{c} BV_{CEO} \\ \\ I_{CBO} \\ I_{EBO} \\ h_{FE} \end{array}$ $\begin{array}{c} V_{CE} \left( sat \right) \\ V_{BE} \left( on \right) \\ f_{T} \end{array}$	$\begin{split} I_{C} = -10 \text{mA}, \ I_{B} = 0 \\ \\ V_{CB} = -30 \text{V}, \ I_{E} = 0 \\ V_{CE} = -5 \text{V}, \ I_{C} = 0 \\ V_{CE} = -2 \text{V}, \ I_{C} = -5 \text{mA} \\ V_{CE} = -2 \text{V}, \ I_{C} = -150 \text{mA} \\ \\ V_{CE} = -2 \text{V}, \ I_{C} = -50 \text{mA} \\ I_{C} = -500 \text{mA}, \ I_{B} = -50 \text{mA} \\ V_{CE} = -2 \text{V}, \ I_{C} = -50 \text{mA} \\ \\ V_{CE} = -50 \text{mA}, \ I_{D} = -50 \text{mA} \\ \\ V_{CE} = -50 \text{mA}, \ I_{D} = -50 \text{mA} \\ \\ V_{CE} = -50 \text{mA}, \ I_{D} = -50 \text{mA} \\ \\ V_{CE} = -50 \text{mA}, \ I_{D} = -50 \text{mA} \\ \\ V_{CE} = -50 \text{mA}, \ I_{D} = -50 \text{mA} \\ \\ V_{CE} = -50 \text{mA}, \ I_{D} = -50 \text{mA} \\ \\ V_{CE} = -50 \text{mA}, \ I_{D} = -50 \text{mA} \\ \\ V_{CE} = -50 \text{mA}, \ I_{D} = -50 \text{mA} \\ \\ V_{CE} = -50 \text{mA}, \ I_{D} = -50 \text{mA} \\ \\ V_{CE} = -50 \text{mA}, \ I_{D} = -50 \text{mA} \\ \\ V_{CE} = -50 \text{mA}, \ I_{D} = -50 \text{mA} \\ \\ V_{CE} = -50 \text{mA}, \ I_{D} = -50 \text{mA} \\ \\ V_{CE} = -50 \text{mA}, \ I_{D} = -50 \text{mA} \\ \\ V_{CE} = -50 \text{mA}, \ I_{D} = -50 \text{mA} \\ \\ V_{CE} = -50 \text{mA}, \ I_{D} = -50 \text{mA} \\ \\ V_{CE} = -50 \text{mA}, \ I_{D} = -50 \text{mA} \\ \\ V_{CE} = -50 \text{mA}, \ I_{D} = -50 \text{mA} \\ \\ V_{CE} = -50 \text{mA} \\ \\$	-45 -60 -80 25 40 40 25	100	-0.1 -0.1 250 160 -0.5 -1	V V μA μA V MHz

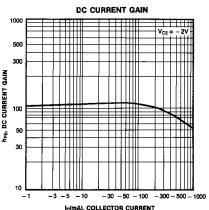


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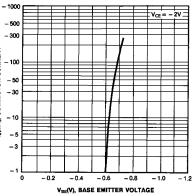
### BC636/638/640

## PNP EPITAXIAL SILICON TRANSISTOR











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